



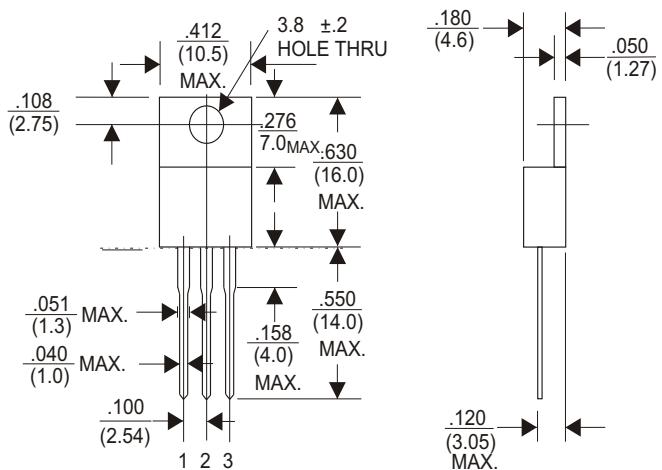
13009 NPN

High Voltage High Speed Switching

Features

- High voltage, high speed switching
- High reliability

TO-220



Dimensions in inches and (millimeters)

Absolute Maximum Rating ($T_c=25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	BV_{CBO}	700	V
Collector-Emitter Voltage	BV_{CEO}	410	V
Emitter-Base Voltage	BV_{EBO}	9	V
Collector Current	I_{C}	12	A
Collector Current pulse	I_{CM}	24	A
Base Current	I_{B}	6	A
Base Current pulse	I_{BM}	12	A
Power Dissipation	P_{D}	2	W
		80	
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 ~ 150	$^\circ\text{C}$

Note: 1. Pulse Test: Pulse Width = 5ms, Duty Cycle $\leq 10\%$

2. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

13009

Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Collector-base breakdown voltage	BV _{CBO}	I _C = 1mA, I _E = 0	700			V
Collector-emitter breakdown voltage	BV _{CEO}	I _C = 5mA, I _B = 0	410		520	V
Emitter-base breakdown voltage	BV _{EBO}	I _E = 0.1mA, I _C = 0	9			V
Collector cut-off current	I _{CBO}	V _{CB} = 700V, I _E = 0			1	mA
Emitter cut-off current	I _{EBO}	V _{EB} = 9V, I _C = 0			1	mA
DC current gain	h _{FE} (1)	V _{CE} = 5V, I _C = 3A	10		35	
	h _{FE} (2)	V _{CE} = 5V, I _C = 2mA	10			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 5A, I _B = 1A			1.0	
		I _C = 8A, I _B = 1.6A			1.5	V
		I _C = 12A, I _B = 3A			3	
Base-emitter on voltage	V _{BE(sat)}	I _C = 5A, I _B = 1A			1.2	
		I _C = 8A, I _B = 1.6A			1.6	V
Transition frequency	f _T	I _C = 0.5A, V _{CE} = 10V, f = 1MHz	4			MHz
Output Capacitance	C _{ob}	V _{CB} = 10V, I _E = 0 f = 0.1MHz		180		pF
Delay Time	t _d	V _C = 125V, I _C = 8A, I _{B1} = I _{B2} = 1.6A t _p = 25μs, Duty ≤ 1%			0.1	μs
Rise Time	t _R				1	μs
Fall Time	t _F				0.7	μs
Switching Time	t _s	I _C = 500mA			0.7	μs

*Pulse Test: Pulse Width = 300μs, Duty Cycle = 2%

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance Junction to Ambient	θ _{JA}	54	°C/W
Thermal Resistance Junction to Case	θ _{JC}	4	°C/W

RATING AND CHARACTERISTIC CURVES (13009)

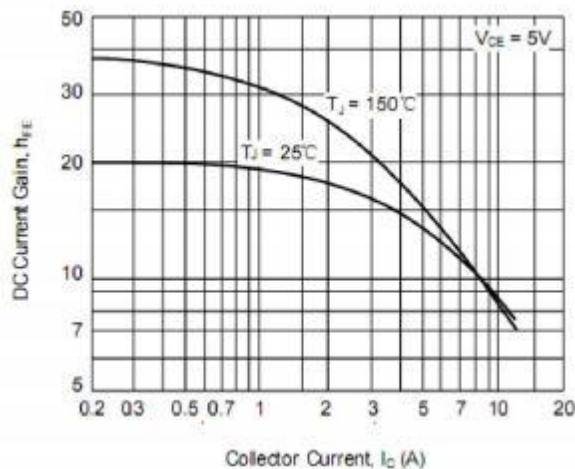


Figure 1. DC current Gain

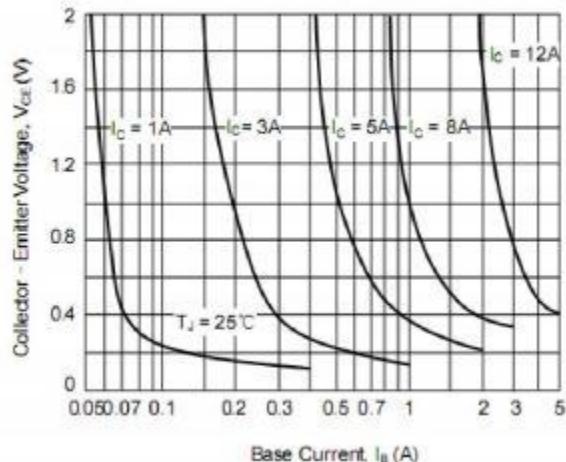


Figure 2. Collector Saturation Region

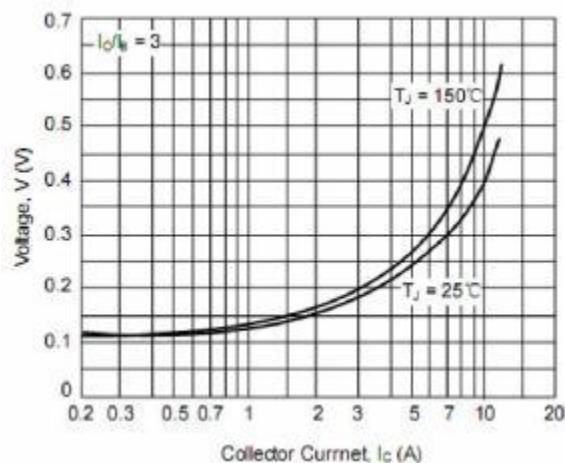


Figure 3. Collector Saturation Voltage

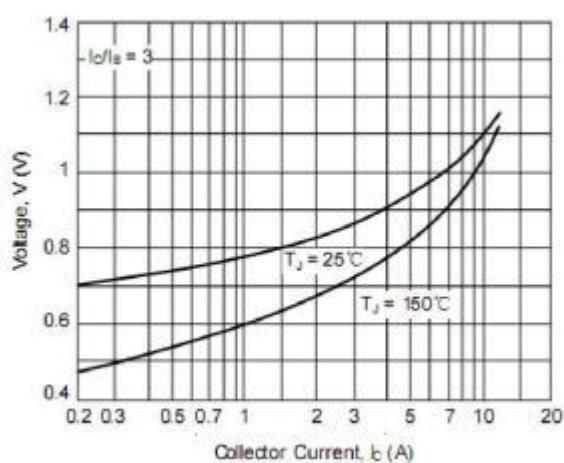


Figure 4. Safe Operating Area Base and

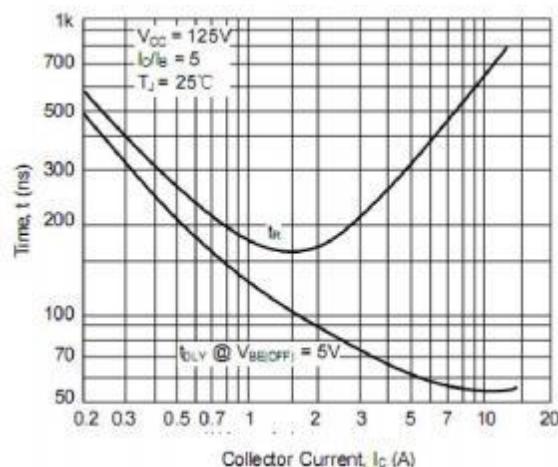


Figure 5. Turn-On Time

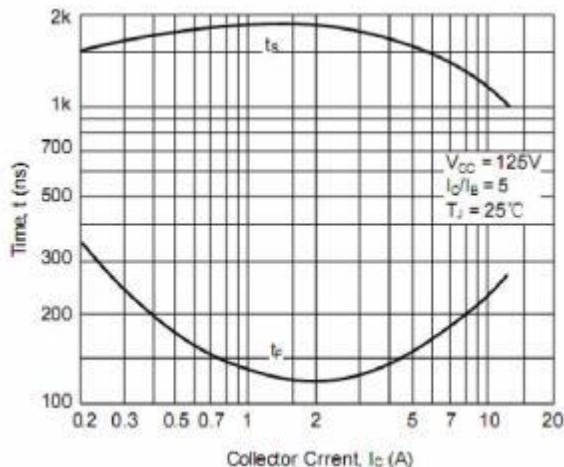


Figure 6. Turn-Off Time

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